

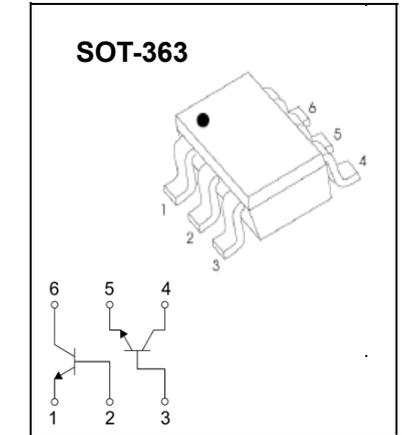
## Plastic-Encapsulate Transistors

DUAL TRANSISTOR (NPN+NPN)

### FEATURES

- Two 2SC2412K chips in a package

MAKING: X3



### MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
I <sub>C</sub>	Collector Current -Continuous	150	mA
P <sub>C</sub>	Collector Power Dissipation	150	mW
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =50μA, I <sub>E</sub> =0	60			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =50μA, I <sub>C</sub> =0	7			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =60V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =7V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	120		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.4	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =12V, I <sub>C</sub> =-2mA, f=100MHz		180		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =12V, I <sub>E</sub> =0, f=1MHz		2.0	3.5	pF

## Typical Characteristics

